PHOTONICS **Research**

InAlGaN superluminescent diodes fabricated on patterned substrates: an alternative semiconductor broadband emitter: publisher's note

Anna Kafar,[1,*] **Szymon Stanczyk,**[1] **Marcin Sarzynski,**[1] **Szymon Grzanka,**[1,2] **Jakub Goss,**[1] **Irina Makarowa,**[2] **Anna Nowakowska-Siwinska,**[2] **Tadek Suski,**[1] **and Piotr Perlin**[1,2]

[1]*Institute of High Pressure Physics, Polish Academy of Sciences, Sokolowska 29/37, 01-142 Warsaw, Poland*
[2]*TopGaN Ltd., Sokolowska 29/37, 01-142 Warsaw, Poland*
**Corresponding author: ak@unipress.waw.pl*

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REFERENCE

1. A. Kafar, S. Stanczyk, M. Sarzynski, S. Grzanka, J. Goss, I. Makarowa, A. Nowakowska-Siwinska, T. Suski, and P. Perlin, "InAlGaN superluminescent diodes fabricated on patterned substrates: an alternative semiconductor broadband emitter," Photon. Res. **5**, A30–A34 (2017).

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